

TECHNICAL DATA DATA SHEET 5433, REV. -

Ultrafast Recovery Die

FEATURES / BENEFITS:

- ✓ Die fabricated on a MIL-PRF-19500 manufacturing line
- ✓ Class H and Class K element evaluation available
- ✓ All ratings are @ T_A = 25 °C unless otherwise specified

ELECTRICAL CHARACTERISTICS:

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage 1C6657 1C6658 1C6659	V _{RWM}	<u>-</u>	100 150 200	V
Max. Average Forward Current	I _{F(AV)}	@ 100°C	15	Α
Die Size	-	-	120	mil
Max. Junction Temperature	T _J	-	-55 to +200	°C
Max. Storage Temperature	T _{stg}	-	-55 to +200	°C

Electrical Characteristics:

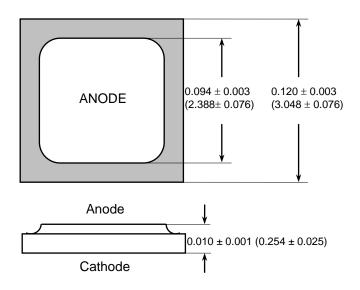
Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 10A, Pulse, T _J = 25 °C	1.0	V
		@ 20A, Pulse, T _J = 25 °C	1.2	
		Duty cycle ≤ 2%, pulse width ≤		
		300μs		
Max. Reverse Current	I _{R1}	$@V_R = V_{RWM}, Pulse,$	10	μΑ
		T _J = 25 °C		
	I _{R2}	$@V_R = V_{RWM}, Pulse,$	1000	μΑ
		T _J = 100 °C		
Reverse Recovery Time	t _{rr}	$I_f = 1A, I_r = 1A, I_{rm} = 100mA$	35	ns
Junction Capacitance	CJ	V_R = 10Vdc, f=1.0MH _Z , V_{SIG} = 50mV	150	pF

ULTRAFAST RECOVERY DIE

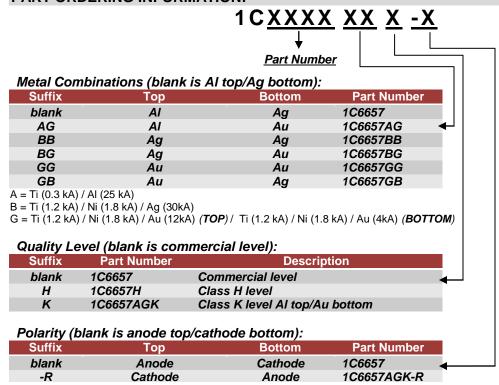
SENSITRON SEMICONDUCTOR

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PACKAGE DIMENSIONS (inches/mm):



PART ORDERING INFORMATION:



SENSITRON SEMICONDUCTOR

1C6657 thru 1C6659
ULTRAFAST RECOVERY DIE

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